

General Purpose Transistor

DESCRIPTION

L2SA1365FLT1G is a mini package silicon PNP epitaxial transistor, it is designed for low frequency voltage application.

FEATURE

- Small collector to emitter saturation voltage.
 $V_{CE(sat)} = -0.3V \text{ max } (@ I_C = -100 \text{ mA}, I_B = -10 \text{ mA})$
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting
- We declare that the material of product compliance with RoHS requirements.

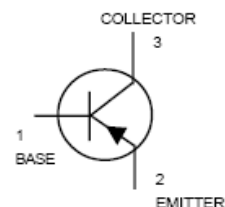
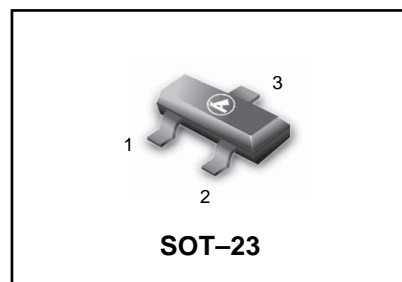
APPLICATION

For Hybrid IC, small type machine low frequency voltage amplify application.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	-50	V
V_{CEO}	Collector to Emitter voltage	-50	V
V_{EBO}	Emitter to Base voltage	-6	V
I_O	Collector current	-200	mA
P_c	Collector dissipation	200	mW
T_j	Junction temperature	+150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 ~ +150	$^\circ\text{C}$

L2SA1235FLT1G



ORDERING INFORMATION

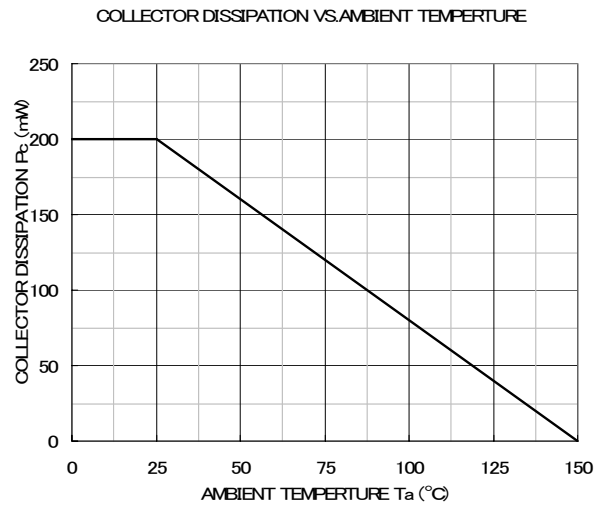
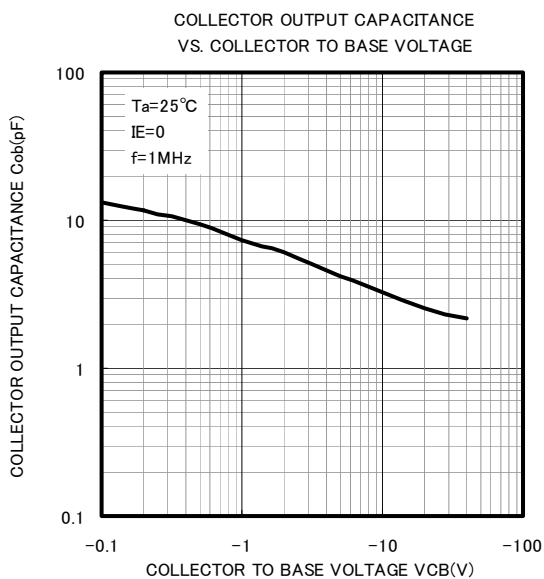
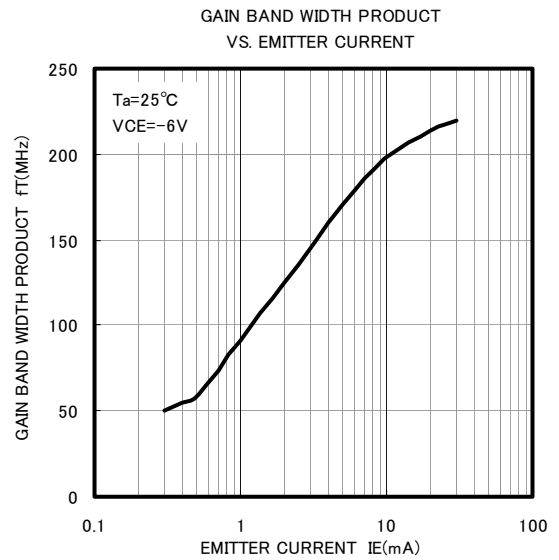
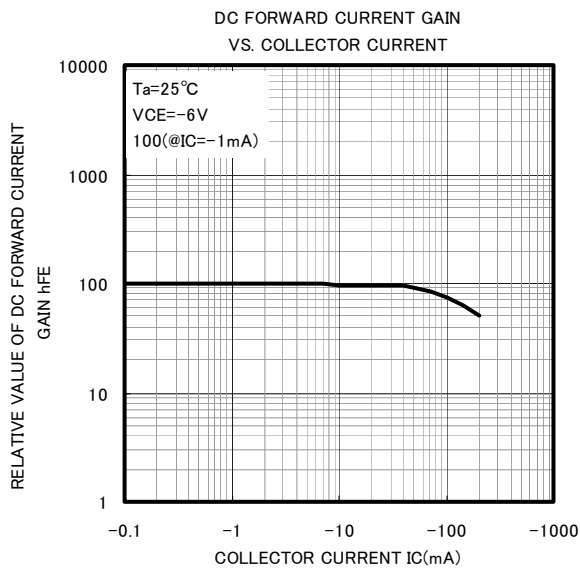
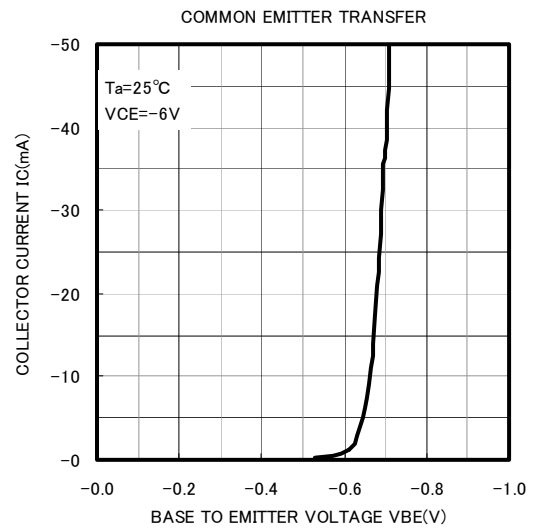
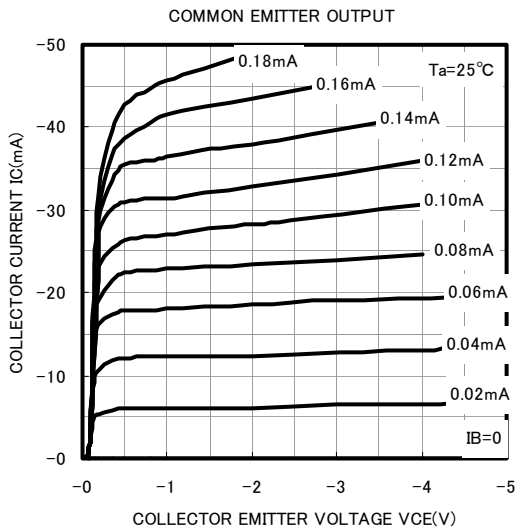
Device	Marking	Shipping
L2SA1235FLT1G	A5F	3000/Tape & Reel
L2SA1235FLT3G	A5F	10000/Tape & Reel

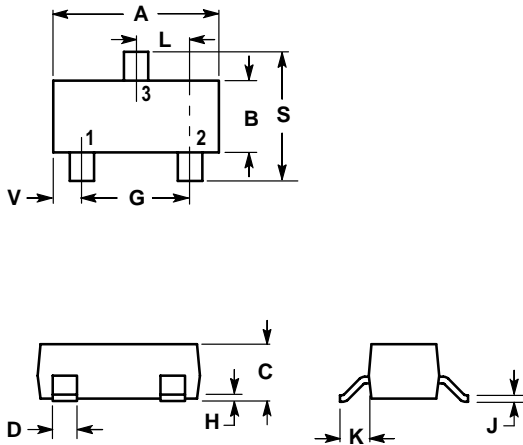
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to E break down voltage	$V(BR)_{CEO}$	$I_C = -100 \mu\text{A}, R_{BE} = \infty$	-50	-	-	V
Collector cut off current	I_{CBO}	$V_{CB} = -50V, I_E = 0\text{mA}$	-	-	-0.1	μA
Emitter cut off current	I_{EBO}	$V_{EB} = -6V, I_C = 0\text{mA}$	-	-	-0.1	μA
DC forward current gain	hFE	$V_{CE} = -6V, I_C = -1\text{mA}$	150	-	800	
DC forward current gain	hFE	$V_{CE} = -6V, I_C = -0.1\text{mA}$	90	-	-	
C to E Saturation Vlotage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$	-	-	-0.3	V
Gain bandwidth product	fT	$V_{CE} = -6V, I_E = 10\text{mA}$	-	200	-	MHz
Collector output capacitance	Cob	$V_{CB} = -6V, I_E = 0, f = 1\text{MHz}$	-	4	-	pF
Noise figure	NF	$V_{CE} = -6V, I_E = 0.3\text{mA}, f = 100\text{Hz}, R_G = 10k\Omega$	-	-	20	dB

※) It shows hFE classification in below table.

Item	E	F	G
h F E Item	150~300	250~500	400~800

L2SA1235FLT1G


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SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

